Bin Liu

List of Publications by Year in descending order

231 papers	5,473 citations	196777 29 h-index	116156 66 g-index
232 all docs	232 docs citations	232 times ranked	8434 citing authors

#	Article	IF	Citations
1	Plasma assisted molecular beam epitaxial growth of GaN with low growth rates and their properties. Chinese Physics B, 2022, 31, 018102.	0.7	4
2	A room-temperature chemiresistive NO2 sensor based on one-step synthesized SnO2 nanospheres functionalized with Pd nanoparticles and rGO nanosheets. Applied Surface Science, 2022, 575, 151698.	3.1	18
3	High-performance sub-10Ânm monolayer black arsenic phosphorus tunneling transistors. Applied Surface Science, 2022, 576, 151705.	3.1	9
4	Epitaxial Growth and Characteristics of Nonpolar a-Plane InGaN Films with Blue-Green-Red Emission and Entire In Content Range. Chinese Physics Letters, 2022, 39, 048101.	1.3	4
5	Achieving Record High External Quantum Efficiency >86.7% in Solarâ€Blind Photoelectrochemical Photodetection. Advanced Functional Materials, 2022, 32, .	7.8	23
6	C-Plane Blue Micro-LED With 1.53 GHz Bandwidth for High-Speed Visible Light Communication. IEEE Electron Device Letters, 2022, 43, 910-913.	2.2	23
7	Light-activated ultrasensitive NO2 gas sensor based on heterojunctions of CuO nanospheres/MoS2 nanosheets at room temperature. Sensors and Actuators B: Chemical, 2022, 368, 132131.	4.0	48
8	Self-Assembly Nanopillar/Superlattice Hierarchical Structure: Boosting AlGaN Crystalline Quality and Achieving High-Performance Ultraviolet Avalanche Photodetector. ACS Applied Materials & Interfaces, 2022, 14, 33525-33537.	4.0	4
9	Evaluation on Temperature-Dependent Transient VT Instability in p-GaN Gate HEMTs under Negative Gate Stress by Fast Sweeping Characterization. Micromachines, 2022, 13, 1096.	1.4	6
10	Improved Optical Properties of Nonpolar AlGaN-Based Multiple Quantum Wells Emitting at 280 nm. IEEE Photonics Journal, 2021, 13, 1-7.	1.0	3
11	2.7-kV AlGaN/GaN Schottky barrier diode on silicon substrate with recessed-anode structure. Solid-State Electronics, 2021, 175, 107953.	0.8	11
12	3.4-kV AlGaN/GaN Schottky Barrier Diode on Silicon Substrate With Engineered Anode Structure. IEEE Electron Device Letters, 2021, 42, 208-211.	2.2	20
13	High Performance Wide Angle DBR Design for Optoelectronic Devices. IEEE Photonics Journal, 2021, 13, 1-6.	1.0	6
14	Hydrogen gas sensor based on SnO2 nanospheres modified with Sb2O3 prepared by one-step solvothermal route. Sensors and Actuators B: Chemical, 2021, 331, 129441.	4.0	48
15	Investigations of Sidewall Passivation Technology on the Optical Performance for Smaller Size GaN-Based Micro-LEDs. Crystals, 2021, 11, 403.	1.0	19
16	Pure-phase Î²-Ga2O3 layers grown on c-plane sapphire by halide vapor phase epitaxy. Superlattices and Microstructures, 2021, 152, 106845.	1.4	9
17	Study of Î²-Ga2O3 films hetero-epitaxially grown on off-angled sapphire substrates by halide vapor phase epitaxy. Materials Letters, 2021, 289, 129411.	1.3	12
18	Progress on AlGaN-based solar-blind ultraviolet photodetectors and focal plane arrays. Light: Science and Applications, 2021, 10, 94.	7.7	193

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19	Influence of plasmonic resonant wavelength on energy transfer from an InGaN quantum well to quantum dots. Applied Physics Letters, 2021, 118, .	1.5	3
20	A room-temperature NO2 gas sensor based on CuO nanoflakes modified with rGO nanosheets. Sensors and Actuators B: Chemical, 2021, 337, 129783.	4.0	132
21	Plasma assisted molecular beam epitaxy growth mechanism of AlGaN epilayers and strain relaxation on AlN templates. Japanese Journal of Applied Physics, 2021, 60, 075504.	0.8	5
22	46.4: Fabrication of InGaN/GaNâ€based nanoâ€LEDs for display applications. Digest of Technical Papers SID International Symposium, 2021, 52, 568-568.	0.1	0
23	Facile synthesis of mesoporous CdS/PbS/SnO2 composites for high-selectivity H2 gas sensor. Sensors and Actuators B: Chemical, 2021, 340, 129924.	4.0	48
24	High-efficiency green micro-LEDs with GaN tunnel junctions grown hybrid by PA-MBE and MOCVD. Photonics Research, 2021, 9, 1683.	3.4	13
25	Growth and nitridation of Î²-Ga2O3 thin films by Sol-Gel spin-coating epitaxy with post-annealing process. Journal of Sol-Gel Science and Technology, 2021, 100, 183-191.	1.1	10
26	Three-dimensional monolithic micro-LED display driven by atomically thin transistor matrix. Nature Nanotechnology, 2021, 16, 1231-1236.	15.6	120
27	1.26 W/mm Output Power Density at 10 GHz for Si₃N₄Passivated H-Terminated Diamond MOSFETs. IEEE Transactions on Electron Devices, 2021, 68, 5068-5072.	1.6	8
28	High quality CVD single crystal diamonds grown on nanorods patterned diamond seed. Diamond and Related Materials, 2021, 119, 108605.	1.8	10
29	1 W/mm Output Power Density for H-Terminated Diamond MOSFETs With Al₂O₃/SiO₂Bi-Layer Passivation at 2 GHz. IEEE Journal of the Electron Devices Society, 2021, 9, 160-164.	1.2	14
30	Microstructural analysis of heteroepitaxial Î²-Ga₂O₃ films grown on (0001) sapphire by halide vapor phase epitaxy. Journal Physics D: Applied Physics, 2021, 54, 014003.	1.3	13
31	NiO/AlGaN interface reconstruction and transport manipulation of p-NiO gated AlGaN/GaN HEMTs. Applied Physics Reviews, 2021, 8, .	5.5	9
32	Surface plasmon coupling regulated CsPbBr₃ perovskite lasers in a metalâ€“insulatorâ€“semiconductor structure. RSC Advances, 2021, 11, 37218-37224.	1.7	6
33	Low-threshold lasing in a plasmonic laser using nanoplate InGaN/GaN. Journal of Semiconductors, 2021, 42, 122803.	2.0	2
34	A Selective Etching Route for Large-Scale Fabrication of Î²-Ga2O3 Micro-/Nanotube Arrays. Nanomaterials, 2021, 11, 3327.	1.9	7
35	Hybrid Light Emitters and UV Solarâ€Blind Avalanche Photodiodes based on IIIâ€Nitride Semiconductors. Advanced Materials, 2020, 32, e1904354.	11.1	34
36	The influence of an AlN seeding layer on nucleation of self-assembled GaN nanowires on silicon substrates. Nanotechnology, 2020, 31, 045604.	1.3	3

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37	Synthesis and Properties of InGaN/GaN Multiple Quantum Well Nanowires on Si (111) by Molecular Beam Epitaxy. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900729.	0.8	4
38	Improved Performance of Hybrid Organic/Inorganic pâ€“n Heterojunction White Lightâ€Emitting Diodes with 4,4â€²â€Cyclohexaneâ€1,1â€diylbis[N , N â€bis(4â€methylphenyl)aniline] as a Multifunctional Hole Transport Layer. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900763.	0.8	0
39	Electronic properties of arsenene nanoribbons for FET application. Optical and Quantum Electronics, 2020, 52, 1.	1.5	3
40	High-Performance Semi-Polar InGaN/GaN Green Micro Light-Emitting Diodes. IEEE Photonics Journal, 2020, 12, 1-7.	1.0	6
41	Improvement of the interfaces in AlGaN/AlN superlattice grown by NH₃ flow-rate modulation epitaxy. Applied Physics Express, 2020, 13, 015511.	1.1	6
42	Electronâ€Beamâ€Driven IIIâ€Nitride Plasmonic Nanolasers in the Deepâ€UV and Visible Region. Small, 2020, 16, 1906205.	5.2	10
43	Approach to Single-Mode Dominated Resonant Emission in GaN-Based Square Microdisks on Si*. Chinese Physics Letters, 2020, 37, 054204.	1.3	1
44	Preparation of vertically aligned GaN@Ga2O3 core-shell heterostructured nanowire arrays and their photocatalytic activity for degradation of Rhodamine B. Superlattices and Microstructures, 2020, 143, 106556.	1.4	18
45	Improved Performance of Hybrid Organic/Inorganic pâ€“n Heterojunction White Lightâ€Emitting Diodes with 4,4â€²â€Cyclohexaneâ€1,1â€diylbis[N,Nâ€bis(4â€methylphenyl)aniline] as a Multifunctional Hole Transport Layer. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 2070029.	0.8	0
46	Different Iâ€“V Behaviors and Leakage Current Mechanisms in AlGaN Solar-Blind Ultraviolet Avalanche Photodiodes. ACS Applied Electronic Materials, 2020, 2, 2716-2720.	2.0	3
47	Misfit epitaxial strain manipulated transport properties in cubic In2O3 hetero-epilayers. Applied Physics Letters, 2020, 117, 102104.	1.5	4
48	Synthesis and Properties of InGaN/GaN Multiple Quantum Well Nanowires on Si (111) by Molecular Beam Epitaxy. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 2070028.	0.8	0
49	Îµ-Ga2O3: A Promising Candidate for High-Electron-Mobility Transistors. IEEE Electron Device Letters, 2020, , 1-1.	2.2	15
50	The optimization of surface plasmon coupling efficiency in InGaN/GaN nanowire based nanolasers. Applied Physics Express, 2020, 13, 085001.	1.1	4
51	Realization of regular resonance mode in GaN-based polygonal microdisks on Si. Journal of Applied Physics, 2020, 127, 113102.	1.1	3
52	Band Alignment and Interface Recombination in NiO/Î²-Ga₂O₃ Type-II p-n Heterojunctions. IEEE Transactions on Electron Devices, 2020, 67, 3341-3347.	1.6	63
53	Highâ€Responsivity Graphene/4Hâ€SiC Ultraviolet Photodetector Based on a Planar Junction Formed by the Dual Modulation of Electric and Light Fields. Advanced Optical Materials, 2020, 8, 2000559.	3.6	19
54	Comparison study of GaN films grown on porous and planar GaN templates*. Chinese Physics B, 2020, 29, 038103.	0.7	4

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55	Do all screw dislocations cause leakage in GaN-based devices?. Applied Physics Letters, 2020, 116, .	1.5	38
56	Charge Transport in Vertical GaN Schottky Barrier Diodes: A Refined Physical Model for Conductive Dislocations. IEEE Transactions on Electron Devices, 2020, 67, 841-846.	1.6	21
57	Plasmon-enhanced photoelectrochemical water splitting by InGaN/GaN nano-photoanodes. Semiconductor Science and Technology, 2020, 35, 025017.	1.0	17
58	Mg acceptor activation mechanism and hole transport characteristics in highly Mg-doped AlGaN alloys. Chinese Physics B, 2020, 29, 058103.	0.7	3
59	1.4-kV Quasi-Vertical GaN Schottky Barrier Diode With Reverse p-n Junction Termination. IEEE Journal of the Electron Devices Society, 2020, 8, 316-320.	1.2	20
60	High performance GaN-based hybrid white micro-LEDs integrated with quantum-dots. Journal of Semiconductors, 2020, 41, 032301.	2.0	2
61	Solar-blind ultraviolet photodetector based on vertically aligned single-crystalline Î²-Ga₂O₃ nanowire arrays. Nanophotonics, 2020, 9, 4497-4503.	2.9	35
62	Semi-polar (20â€“21) InGaN/GaN multiple quantum wells grown on patterned sapphire substrate with internal quantum efficiency up to 52 per cent. Applied Physics Express, 2020, 13, 091002.	1.1	7
63	Fabrication and Characterization of GaN-Based Micro-LEDs on Silicon Substrate[*]. Chinese Physics Letters, 2019, 36, 088501.	1.3	4
64	Electrically Injected Hybrid Organic/Inorganic III-Nitride White Light-Emitting Diodes Based on Rubrene/(InGaN/GaN) Multiple-Quantum-Wells P-N Junction. IEEE Photonics Journal, 2019, 11, 1-8.	1.0	0
65	A High-Performance SiO₂/SiN _x 1-D Photonic Crystal UV Filter Used for Solar-Blind Photodetectors. IEEE Photonics Journal, 2019, 11, 1-7.	1.0	3
66	Single-crystal GaN layer converted from Î²-Ga₂O₃films and its application for free-standing GaN. CrystEngComm, 2019, 21, 1224-1230.	1.3	10
67	23.3: Invited Paper: Hybrid IIIâ€Nitride/Nanocrystals White Lightâ€Emitting Diodes. Digest of Technical Papers SID International Symposium, 2019, 50, 225-227.	0.1	0
68	Study on the nitridation of Î²-Ga₂O₃ films*. Chinese Physics B, 2019, 28, 088103.	0.7	1
69	A simulation study on the enhancement of the efficiency of GaN-based blue light-emitting diodes at low current density for micro-LED applications. Materials Research Express, 2019, 6, 105915.	0.8	25
70	Optical Performance of Top-Down Fabricated AlGaN Nanorod Arrays with Multi-Quantum Wells Embedded. Nanoscale Research Letters, 2019, 14, 170.	3.1	2
71	Performance of Monolayer Blue Phosphorene Double-Gate MOSFETs from the First Principles. ACS Applied Materials & Interfaces, 2019, 11, 20956-20964.	4.0	39
72	Synthesis and characterization of Î² -Ga ₂ O ₃ @GaN nanowires. Chinese Physics B, 2019, 28, 028104.	0.7	6

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73	Observation and Modeling of Leakage Current in AlGaN Ultraviolet Light Emitting Diodes. IEEE Photonics Technology Letters, 2019, 31, 1697-1700.	1.3	4
74	Porous single-crystal GaN films obtained by direct top-down nitridation of bulk and film Î²-Ga2O3. Superlattices and Microstructures, 2019, 126, 98-102.	1.4	1
75	Single-crystalline GaN porous template prepared by a simple top-down nitridation technique. Materials Letters, 2019, 240, 121-123.	1.3	5
76	Homo-epitaxial growth of high crystal quality GaN thin films by plasma assistedâ€“molecular beam epitaxy. Journal of Crystal Growth, 2019, 506, 30-35.	0.7	9
77	Influence of high Mg doping on the microstructural and opto-electrical properties of AlGaN alloys. Superlattices and Microstructures, 2018, 119, 150-156.	1.4	5
78	The Study on the Droop Effect in the InGaN/AlGaInN MQWs With Lattice-Matched AlGaN/InGaN Superlattices Barrier by Highly Excited Photoluminescence Measurement. IEEE Photonics Journal, 2018, 10, 1-9.	1.0	7
79	Study of GaN nanorods converted from Î²-Ga2O3. Superlattices and Microstructures, 2018, 117, 235-240.	1.4	4
80	Stress-free InN nanowires grown on graphene by sublimation method. Materials Letters, 2018, 211, 165-167.	1.3	1
81	Hybrid Cyan Nitride/Red Phosphors White Light-Emitting Diodes With Micro-Hole Structures. IEEE Photonics Journal, 2018, 10, 1-8.	1.0	9
82	Enhanced p-type conduction in AlGaN grown by metal-source flow-rate modulation epitaxy. Applied Physics Letters, 2018, 113, .	1.5	17
83	The growth of 3C-SiC on Si substrate using a SiCN buffer layer. Thin Solid Films, 2018, 662, 168-173.	0.8	5
84	Growth ofÎ²-Ga₂O₃Films on Sapphire by Hydride Vapor Phase Epitaxy. Chinese Physics Letters, 2018, 35, 058101.	1.3	22
85	Structural characterization of Al _{0.55} Ga _{0.45} N epitaxial layer determined by high resolution x-ray diffraction and transmission electron microscopy. Chinese Physics B, 2017, 26, 047801.	0.7	3
86	Structural and optical properties of Al x Ga 1â^'x N (0.33Ââ‰ÂxÂâ‰Â0.79) layers on high-temperature AlN interlayer grown by metal organic chemical vapor deposition. Superlattices and Microstructures, 2017, 101, 144-151.	1.4	7
87	Shape-Evolution Control of hybrid perovskite CH3NH3PbI3 crystals via solvothermal synthesis. Journal of Crystal Growth, 2017, 459, 167-172.	0.7	18
88	The formation of SiCN film on Si substrate by constant-source diffusion. Thin Solid Films, 2017, 642, 124-128.	0.8	2
89	Manipulable and Hybridized, Ultralowâ€Threshold Lasing in a Plasmonic Laser Using Elliptical InGaN/GaN Nanorods. Advanced Functional Materials, 2017, 27, 1703198.	7.8	23
90	Tunneling-Hopping Transport Model for Reverse Leakage Current in InGaN/GaN Blue Light-Emitting Diodes. IEEE Photonics Technology Letters, 2017, 29, 1447-1450.	1.3	14

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91	Fabrication of AlGaN nanorods with different Al compositions for emission enhancement in UV range. Nanotechnology, 2017, 28, 385205.	1.3	16
92	Photoluminescence Study of the Photoinduced Phase Separation in Mixed-Halide Hybrid Perovskite CH3NH3Pb(BrxI1â^'x)3 Crystals Synthesized via a Solvothermal Method. Scientific Reports, 2017, 7, 17695.	1.6	18
93	A Simple Deposition Method for Self-Assembling Single Crystalline Hybrid Perovskite Nanostructures. Chinese Physics Letters, 2017, 34, 068103.	1.3	1
94	Study of LED Thermal Resistance and TIM Evaluation Using LEDs With Built-in Sensor. IEEE Photonics Technology Letters, 2017, 29, 1856-1859.	1.3	1
95	Enhanced InGaN/GaN photoelectrodes for visibleâ€lightâ€driven hydrogen generation by surface roughening. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 2704-2708.	0.8	1
96	Properties of a CdZnO/ZnO multiple quantum-well light-emitting diode. Journal of the Korean Physical Society, 2016, 69, 1219-1224.	0.3	2
97	Improvement of color conversion and efficiency droop in hybrid light-emitting diodes utilizing an efficient non-radiative resonant energy transfer. Applied Physics Letters, 2016, 109, .	1.5	11
98	Band Edge Emission Improvement by Energy Transfer in Hybrid III-Nitride/Organic Semiconductor Nanostructure. Chinese Physics Letters, 2016, 33, 108101.	1.3	0
99	High Color Rendering Index Hybrid IIIâ€Nitride/Nanocrystals White Lightâ€Emitting Diodes. Advanced Functional Materials, 2016, 26, 36-43.	7.8	58
100	Single nanowire green InGaN/GaN light emitting diodes. Nanotechnology, 2016, 27, 435205.	1.3	16
101	High-Brightness Polarized Green InGaN/GaN Light-Emitting Diode Structure with Al-Coated p-GaN Grating. ACS Photonics, 2016, 3, 1912-1918.	3.2	28
102	Epitaxy and optical properties of InGaN/GaN multiple quantum wells on GaN hexagonal pyramids template. Materials Letters, 2016, 180, 298-301.	1.3	3
103	Morphological evolution and characterization of GaN pyramid arrays fabricated by photo-assisted chemical etching. Superlattices and Microstructures, 2016, 100, 1249-1255.	1.4	3
104	Reverse Leakage Current Characteristics of GaN/InGaN Multiple Quantum-Wells Blue and Green Light-Emitting Diodes. IEEE Photonics Journal, 2016, 8, 1-7.	1.0	10
105	Iridium Oxideâ€Assisted Plasmonâ€Induced Hot Carriers: Improvement on Kinetics and Thermodynamics of Hot Carriers. Advanced Energy Materials, 2016, 6, 1501339.	10.2	111
106	Design and fabrication of UV band-pass filters based on SiO2/Si3N4 dielectric distributed bragg reflectors. Applied Surface Science, 2016, 364, 886-891.	3.1	37
107	Polarized Emission From InGaN/GaN Single Nanorod Light-Emitting Diode. IEEE Photonics Technology Letters, 2016, 28, 721-724.	1.3	9
108	AlGaN-Based Multiple Quantum Well Deep Ultraviolet Light-Emitting Diodes With Polarization Doping. IEEE Photonics Journal, 2016, 8, 1-7.	1.0	12

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109	Great enhancement in the excitonic recombination and light extraction of highly ordered InGaN/GaN elliptic nanorod arrays on a wafer scale. Nanotechnology, 2016, 27, 015301.	1.3	31
110	Characteristics of deep ultraviolet AlGaN-based light emitting diodes with p-hBN layer. Physica E: Low-Dimensional Systems and Nanostructures, 2016, 75, 52-55.	1.3	16
111	Significant improvements in InGaN/GaN nano-photoelectrodes for hydrogen generation by structure and polarization optimization. Scientific Reports, 2016, 6, 20218.	1.6	27
112	Enhanced non-radiative energy transfer in hybrid III-nitride structures. Applied Physics Letters, 2015, 107, 121108.	1.5	5
113	Asymmetric tunneling model of forward leakage current in GaN/InGaN light emitting diodes. AIP Advances, 2015, 5, 087151.	0.6	12
114	Optical polarization characteristics of c-plane InGaN/GaN asymmetric nanostructures. Journal of Applied Physics, 2015, 118, .	1.1	15
115	Effect of lattice defects on the property of GaN crystal: A molecular dynamics simulation study. Superlattices and Microstructures, 2015, 88, 679-684.	1.4	5
116	Effect of High-Temperature Annealing on Yellow and Blue Luminescence of Undoped GaN. Chinese Physics Letters, 2015, 32, 097804.	1.3	2
117	OneâEDimensional Hybrid Nanostructures for Heterogeneous Photocatalysis and Photoelectrocatalysis. Small, 2015, 11, 2115-2131.	5.2	213
118	Enhanced opto-electrical properties of graphene electrode InGaN/GaN LEDs with a NiOx inter-layer. Solid-State Electronics, 2015, 109, 47-51.	0.8	7
119	Bloch surface plasmon enhanced blue emission from InGaN/GaN light-emitting diode structures with Al-coated GaN nanorods. Nanotechnology, 2015, 26, 125201.	1.3	6
120	Investigation of surface-plasmon coupled red light emitting InGaN/GaN multi-quantum well with Ag nanostructures coated on GaN surface. Journal of Applied Physics, 2015, 117, .	1.1	10
121	<italic>In-Situ</italic> Measurement of Junction Temperature and Light Intensity of Light Emitting Diodes With an Internal Sensor Unit. IEEE Electron Device Letters, 2015, 36, 1082-1084.	2.2	11
122	Room temperature plasmonic lasing in a continuous wave operation mode from an InGaN/GaN single nanorod with a low threshold. Scientific Reports, 2015, 4, 5014.	1.6	42
123	Temporally and spatially resolved photoluminescence investigation of (112Â¯2) semi-polar InGaN/GaN multiple quantum wells grown on nanorod templates. Applied Physics Letters, 2014, 105, .	1.5	22
124	GaN hexagonal pyramids formed by a photo-assisted chemical etching method. Chinese Physics B, 2014, 23, 058101.	0.7	7
125	Coherent nanocavity structures for enhancement in internal quantum efficiency of III-nitride multiple quantum wells. Applied Physics Letters, 2014, 104, 161108.	1.5	9
126	Fabrication of wafer-scale nanopatterned sapphire substrate by hybrid nanoimprint lithography. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2014, 32, .	0.6	7

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127	Effect of the band structure of InGaN/GaN quantum well on the surface plasmon enhanced light-emitting diodes. Journal of Applied Physics, 2014, 116, 013101.	1.1	7
128	Temperature dependence of non-radiative energy transfer in hybrid structures of InGaN/GaN nanorods and F8BT films. Applied Physics Letters, 2014, 105, 171111.	1.5	6
129	Enhancement in solar hydrogen generation efficiency using InGaN photoelectrode after surface roughening treatment with nano-sized Ni mask. Chinese Physics B, 2014, 23, 096203.	0.7	1
130	Synthesis and Growth Mechanism: A Novel Fishing Rod-Shaped GaN Nanorods. Chinese Physics Letters, 2014, 31, 056802.	1.3	1
131	Design of deep ultraviolet light-emitting diodes with staggered AlGaN quantum wells. Physica E: Low-Dimensional Systems and Nanostructures, 2014, 62, 55-58.	1.3	21
132	High-temperature humidity sensors based on WO₃â€“SnO₂ composite hollow nanospheres. Journal of Materials Chemistry A, 2014, 2, 6854-6862.	5.2	84
133	Characteristics of nanoporous InGaN/GaN multiple quantum wells. Superlattices and Microstructures, 2014, 71, 38-45.	1.4	8
134	Spatially localised luminescence emission properties induced by formation of ring-shaped quasi-potential trap around V-pits in InGaN epi-layers. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 2823-2827.	0.8	11
135	Room temperature continuousâ€“wave green lasing from an InGaN microdisk on silicon. Scientific Reports, 2014, 4, 7250.	1.6	48
136	Study on The Optical Properties of GaN-Based Multiple Quantum Well Embedded in Nanostructures. , 2014, , .		0
137	Analysis of magnetic structures of iron nitrides by Landau's theory of second-order phase transitions. AIP Advances, 2013, 3, .	0.6	13
138	Cobaltâ€“Carbon Complexes Induced Ferromagnetism in Chemically Modified Perovskite Dilute Magnetic Complex Oxides. Journal of Physical Chemistry C, 2013, 117, 18258-18265.	1.5	5
139	An efficient In_{0.30}Ga_{0.70}N photoelectrode by decreasing the surface recombination centres in a H₂SO₄ aqueous solution. Journal Physics D: Applied Physics, 2013, 46, 345103.	1.3	6
140	Effect of the V/III ratio during buffer layer growth on the yellow and blue luminescence in undoped GaN epilayer. Science China: Physics, Mechanics and Astronomy, 2013, 56, 1694-1698.	2.0	3
141	Temperature dependence of the point defect properties of GaN thin films studied by terahertz time-domain spectroscopy. Science China: Physics, Mechanics and Astronomy, 2013, 56, 2059-2064.	2.0	5
142	Great emission enhancement and excitonic recombination dynamics of InGaN/GaN nanorod structures. Applied Physics Letters, 2013, 103, .	1.5	38
143	Exploitation of Polarization in Back-Illuminated AlGaN Avalanche Photodiodes. IEEE Photonics Technology Letters, 2013, 25, 1510-1513.	1.3	25
144	Obvious improvement of light extraction obtained by anodic aluminum oxide coverage on GaN surface. Applied Physics A: Materials Science and Processing, 2013, 110, 35-39.	1.1	3

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145	Comprehensive study of the metal-insulator transition in pulsed laser deposited epitaxial VO2 thin films. Journal of Applied Physics, 2013, 113, .	1.1	134
146	Hybrid III-Nitride/Organic Semiconductor Nanostructure with High Efficiency Nonradiative Energy Transfer for White Light Emitters. Nano Letters, 2013, 13, 3042-3047.	4.5	65
147	Investigation of surface plasmon coupling with the quantum well for reducing efficiency droop in GaN-based light emitting diodes. Journal of Applied Physics, 2013, 114, .	1.1	14
148	Investigation of localization effect in GaN-rich InGaN alloys and modified band-tail model. Bulletin of Materials Science, 2013, 36, 619-622.	0.8	6
149	Large-scale fabrication and luminescence properties of GaN nanostructures by a soft UV-curing nanoimprint lithography. Nanotechnology, 2013, 24, 405303.	1.3	29
150	A Band-Gap Energy Model of the Quaternary Alloy In _x Ga _y Al _{1â^' x â^' y} N using Modified Simplified Coherent Potential Approximation. Chinese Physics Letters, 2013, 30, 076101.	1.3	5
151	Roles of V/III ratio and mixture degree in GaN growth: CFD and MD simulation study. Chinese Physics B, 2013, 22, 017801.	0.7	8
152	High-Efficiency InGaN/GaN Nanorod Arrays by Temperature Dependent Photoluminescence. Chinese Physics Letters, 2013, 30, 078502.	1.3	3
153	Suppression of thermal conductivity in InxGa1â^'xN alloys by nanometer-scale disorder. Applied Physics Letters, 2013, 102, 121906.	1.5	53
154	Fabrication of two-dimensional InGaN/GaN photonic crystal structure using a modified nanosphere lithography technique. Applied Physics Letters, 2013, 102, .	1.5	19
155	The enhancement of light-emitting efficiency using GaN-based multiple quantum well light-emitting diodes with nanopillar arrays. Chinese Physics B, 2013, 22, 088102.	0.7	4
156	High-indium-content InGaN quantum-well structure grown pseudomorphically on a strain-relaxed InGaN template layer. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2012, 30, 030603.	0.6	5
157	Indium-rich InGaN epitaxial layers grown pseudomorphically on a nano-sculpted InGaN template. Optics Express, 2012, 20, 8093.	1.7	8
158	Characteristics of polarization-doped N-face III-nitride light-emitting diodes. Applied Physics Letters, 2012, 100, 073507.	1.5	20
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